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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	09/814,023		
		Filing Date	03/20/2001		
		First Named Inventor:	Lynn Cai		
		Examiner name: J. Mancuso	GROUP: 2623		
Sheet	1	of	1	Attorney Docket Number	NTI-006

U.S. PUBLISHED APPLICATION DOCUMENTS

Examiner Initials*	Cited No. ¹	U.S. Patent Document Number	Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines Where Relevant Info. Appear

U.S. PATENT DOCUMENTS

Examiner Initials*	Cited No. ¹	U.S. Patent Document Number	Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines Where Relevant Info. Appear
S.A	E1	4809341		Matsui et al.	02/28/1989	
S.A	E2	5795688		Burdorf et al.	08/18/1998	
S.A	E3	5965306		Mansfield et al.	10/12/1999	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cited No. ¹	Foreign Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines Where Relevant Info. Appear	T ⁶
Office ³	Number ⁴	Kind Code ⁵ (if known)					
S.A	F1	WO	99/14706		Ting et al.	03/25/1999	
S.A	F2	JP	2001056306		Ichiro	02/27/2001	
S.A	F3	EP	0 306 275		Yamada et al.	03/08/1989	
S.A	F4	DE	100 37 697		Aghajan	03/15/2001	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	DATE CONSIDERED

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¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

- ☒ This statement qualifies under 37 C.F.R. § 1.97, subsection (b) because (check all that apply):
- ☐ (1) It is being filed within 3 months of the application filing date and is other than a continued prosecution application under § 1.53(d)
-- OR --
 - ☐ (2) It is being filed within 3 months of entry of a national stage
-- OR --
 - ☒ (3) It is being filed before the mail date of the first Office Action on the merits.
-- OR --
 - ☐ (4) It is being filed before the mailing of a first Office Action after the filing of a request for continued examination under § 1.114
- ☐ 37 C.F.R. § 1.97(c). If this statement is being filed after the period specified in § 1.97(b), but before the mailing date of the earlier of a final office action under § 1.113, a notice of allowance under § 1.311, or an action that otherwise closes prosecution in the application, then:
- ☐ a certification as specified in § 1.97(e) is provided below; **or**
 - ☐ a fee of \$180.00 as set forth in § 1.17(p) is authorized below, enclosed, or included with the payment of other papers filed together with this statement.
- ☐ 37 C.F.R. § 1.97(d). If this statement is being filed after the period specified in § 1.97(c), but on or before payment of the issue fee, then:
- A. a certification as specified in § 1.97(e) is completed below; **and**
 - B. a fee of \$180.00 as set forth in § 1.17(p) is authorized below, enclosed, or included with the payment of other papers filed together with this statement.
- ☒ **Fee Authorization.** The Commissioner is hereby authorized to charge any additional fees or credit any overpayment associated with this communication to Deposit Account No. 50-0574 (Docket No. NTI-006).


Respectfully submitted,

BEVER, HOFFMAN & HARMS, LLP

Dated: 2-7-03

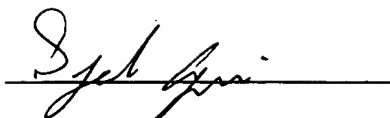
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Jeanette S. Harms, Reg. No. 35,537

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Customer No. 29477

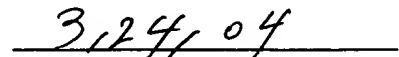
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		Applicant CAI, Lynn		Group 2623		
		Filing Date 3/20/2001				
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
S.A	6,130,750	10/10/2000	Ausschnitt, et al.	356	401	8/28/1997
S.A	6,346,426 B1	2/12/2002	Toprac, et al.	438	8	11/17/2000

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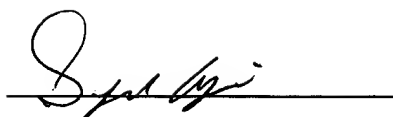


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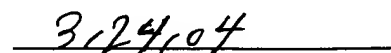
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		Filing Date 3/20/2001				
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
S.A	2002/0164064 A1	11/7/2002	Karklin, et al.	382	145	3/20/2001
S.A	2002/0164065 A1	11/7/2002	Cai, et al.	382	149	3/20/2001

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INFORMATION DISCLOSURE CITATION  PTO-1449	Atty. Docket No. NTI-006 Applicant CAI, Lynn Filing Date 3/20/2001	Serial No. 09/814,023 Group 2623 RECEIVED DEC 10 2002 Technology Center 2000
	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
EXAMINER'S INITIALS	CITATION	
<i>S.A</i>	Lin, B.J., et al., "Single-Level Electric Testsites for Phase-Shifting Masks", SPIE, Vol. 1673, pp. 221-228, March 9-11, 1992.	

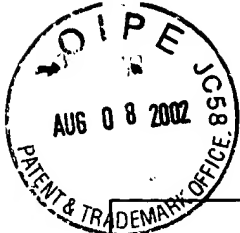
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SHEET 1 of 3

INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. NTI-006	Serial No. 09/814,023
	Applicant CAI, Lynn	RECEIVED AUG 13 2002
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U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
S.A	6,016,357	1/18/2000	Neary, et al.	382	144	6/16/1997
	6,023,328	2/8/2000	Pierrat	356	237.4	2/23/1998
	6,076,465	6/20/2000	Vacca, et al.	101	481	9/19/1997
	6,091,845	7/18/2000	Pierrat, et al.	382	144	2/24/1998
	6,272,236	8/7/2001	Pierrat, et al.	382	144	7/18/2000
	6,334,209 B1	12/25/2001	Hashimoto, et al.	716	21	9/2/1999
	2002/0019729 A1	2/14/2002	Chang, et al.	703	6	8/7/1998

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SHEET 2 of 3**INFORMATION DISCLOSURE
CITATION****PTO-1449****Atty. Docket No.**

NTI-006

Serial No.

09/814,023

Applicant

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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
S.A	WO 97/13370	4/10/1997	WO			<input type="checkbox"/>	<input type="checkbox"/>
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	WO 98/45685	10/15/1998	WO			<input type="checkbox"/>	<input type="checkbox"/>
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SHEET 3 of 3

INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. NTI-006	Serial No. 09/814,023
	Applicant CAI, Lynn	RECEIVED AUG 13 2002
	Filing Date 3/20/2001	Group 3742
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EXAMINER'S INITIALS	CITATION
S.A	Spence, C., et al., "Detection of 60(degree) Phase Defects on Alternating PSMs", Advanced Micro Devices, KLA-Tencor, DuPont RTC (2 pages).
	Ogawa, K., et al., "Phase Defect Inspection by Differential Interference", Lasertec Corporation (12 pages).
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	Hemar, S., et al., "Finding Killer CD Variations by Full-Reticle CD Mapping", Microlithography World, pp. 4, 6, 8 & 10 (Summer 2000).

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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No.	Serial No.
	NTI-006	09/814,023
	Applicant	
	CAI, Lynn	
	Filing Date	Group
	3/20/2001	3742

U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
S.A	6,081,659	6/27/2000	Garza, et al.	395	500.22	4/26/1999
S.A	6,171,731 B1	1/9/2001	Medvedeva, et al.	430	5	1/20/1999

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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. NTI-006	Serial No. 09/814,023
	Applicant CAI, Lynn	
	Filing Date 3/20/2001	Group 3742

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITATION
D.A.	Adam, K., et al., "Simplified Models for Edge Transitions in Rigorous Mask Modeling", University of California Berkeley (40 pages).
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↓	Balasinski, A., et al., "Comparison of Mask Writing Tools and Mask Simulations for 0.16um Devices", IEEE, SEMI Advanced Semiconductor Manufacturing Conference, pp. 372-377 (1999).

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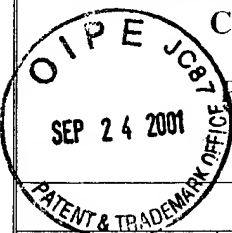
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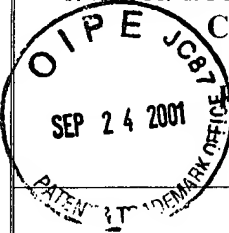
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		APPLICANT Cai, et al.				
		FILING DATE 3/20/01		GROUP 3742		
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
S.A	5,326,659	7/5/94	Liu, et al.	430	5	3/5/92
	5,340,700	8/23/94	Chen, et al.	430	312	11/3/93
	5,432,714	7/11/95	Chung, et al.	364	525	9/2/94
	5,572,598	11/5/96	Wihl, et al.	382	144	2/25/94
	5,795,688	8/18/98	Burdorf, et al.	430	30	8/14/96
	5,801,954	9/1/98	Le, et al.	364	488	4/24/96
	5,804,340	9/8/98	Garza, et al.	430	5	12/23/96
	5,815,685	9/29/98	Kamon	395	500	9/15/95
	5,825,647	10/20/98	Tsudaka	364	167.03	3/12/96
	5,849,440	12/15/98	Lucas, et al.	430	5	1/29/97
	5,862,058	1/19/99	Samuels, et al.	364	491	5/16/96
	5,900,338	5/4/99	Garza, et al.	430	5	8/15/97
	6,009,250	12/28/99	Ho, et al.	395	500.06	9/30/97
	6,009,251	12/28/99	Ho, et al.	395	500.06	9/30/97
6,011,911	1/4/00	Ho, et al.	395	500.06	9/30/97	
6,078,738	6/20/00	Garza, et al.	395	500.22	5/8/97	
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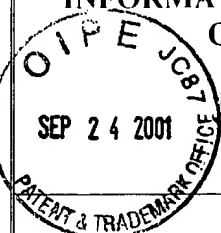

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			FILING DATE 3/20/01		GROUP 3742		
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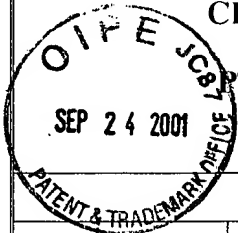
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	APPLICANT Cai, et al.		
	FILING DATE 3/20/01	GROUP 3742	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
S.A	Brunner, T. et al., "Approximate Models For Resist Processing Effects", <i>SPIE</i> , Vol. 2726, pp. 198-207, March 1996.		
	Casey, Jr., J.D. et al., "Chemically Enhanced FIB Repair Of Opaque Defects On Molybdenum Silicide Photomasks", <i>SPIE</i> , Vol. 3236, pp. 487-497 (1997).		
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	Kubota, H. et al., "A Fast Method Of Simulating Resist Pattern Contours Based On Mean Inhibitor Concentration", <i>Jpn. J. Appl. Phys.</i> , Vol. 37, pp. 5815-5820 (1998).		
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EXAMINER <i>S. J. [Signature]</i>	DATE CONSIDERED <i>3/24/04</i>		

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EXAMINER <i>S.M.</i>	DATE CONSIDERED <i>3.24.04</i>	

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S.A.	Wiley, J. et al., "The Effect Of Off-Axis Illumination On The Printability Of Opaque And Transparent Reticle Defects", <i>SPIE</i> , Vol. 2512, pp. 432-440 (1995).	
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